

N-Channel 100-V (D-S) MOSFET

Key Features:

- Low $r_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed

Typical Applications:

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

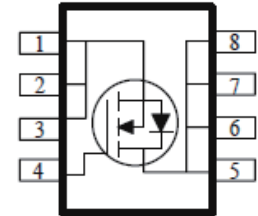
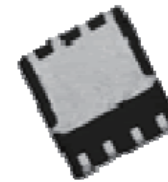
PRODUCT SUMMARY

V_{DS} (V)	$r_{DS(on)}$ (m Ω)	I_D (A)
100	15 @ $V_{GS} = 10V$	15
	19 @ $V_{GS} = 5.5V$	14

DFN5X6-8L



RoHS
COMPLIANT
HALOGEN
FREE



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ^a	I_D	15	A
		13	
Pulsed Drain Current ^b	I_{DM}	50	
Continuous Source Current (Diode Conduction) ^a	I_S	7.1	A
Power Dissipation ^a	P_D	5	W
		3.2	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient ^a	$R_{\theta JA}$	25	$^\circ\text{C/W}$
		65	

Notes

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

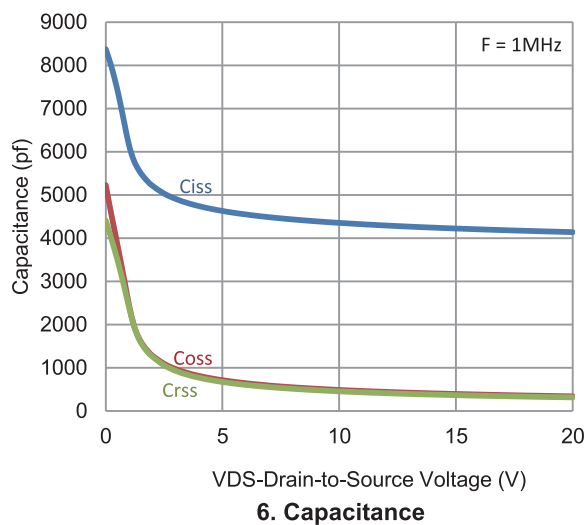
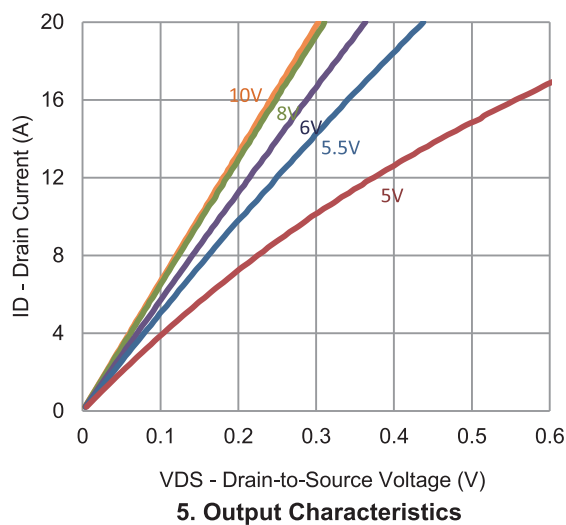
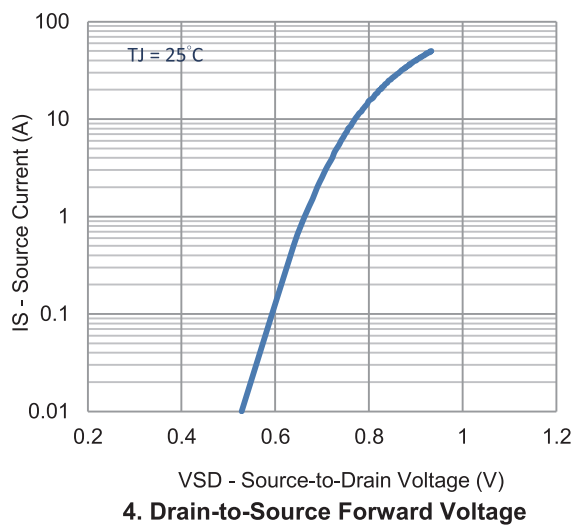
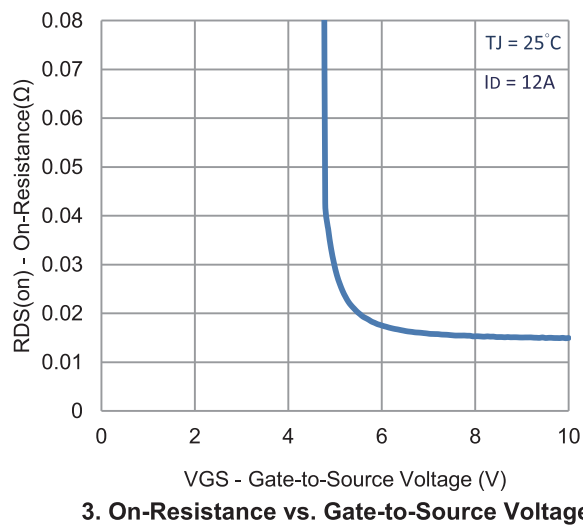
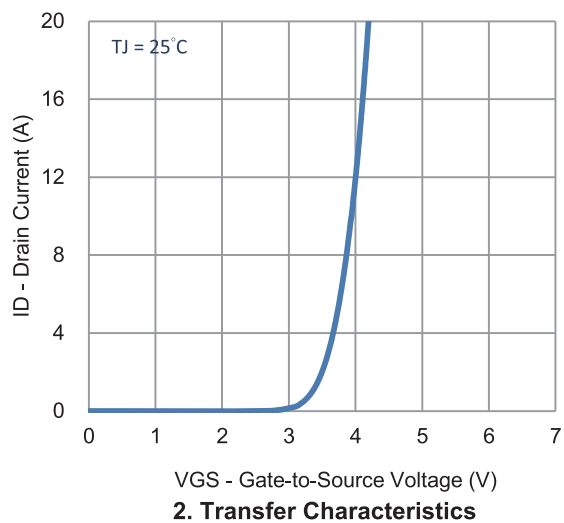
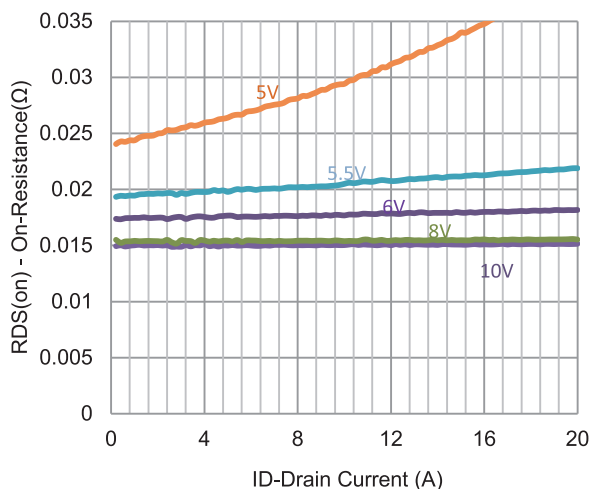
Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80 V, V_{GS} = 0 V$			1	μA
		$V_{DS} = 80 V, V_{GS} = 0 V, T_J = 55^\circ C$			25	
On-State Drain Current	$I_{D(on)}$	$V_{DS} = 5 V, V_{GS} = 10 V$	25			A
Drain-Source On-Resistance	$r_{DS(on)}$	$V_{GS} = 10 V, I_D = 12 A$			15	m Ω
		$V_{GS} = 5.5 V, I_D = 10.7 A$			19	
Forward Transconductance	g_{fs}	$V_{DS} = 15 V, I_D = 12 A$		20		S
Diode Forward Voltage	V_{SD}	$I_S = 3.6 A, V_{GS} = 0 V$		0.73		V
Dynamic						
Total Gate Charge	Q_g	$V_{DS} = 50 V, V_{GS} = 5.5 V, I_D = 12 A$		56		nC
Gate-Source Charge	Q_{gs}			15		
Gate-Drain Charge	Q_{gd}			36		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS} = 50 V, R_L = 4.2 \Omega, I_D = 12 A,$ $V_{GEN} = 10 V, R_{GEN} = 6 \Omega$		26		ns
Rise Time	t_r			56		
Turn-Off Delay Time	$t_{d(off)}$			126		
Fall Time	t_f			61		
Input Capacitance	C_{iss}	$V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz$		4221		pF
Output Capacitance	C_{oss}			392		
Reverse Transfer Capacitance	C_{rss}			364		

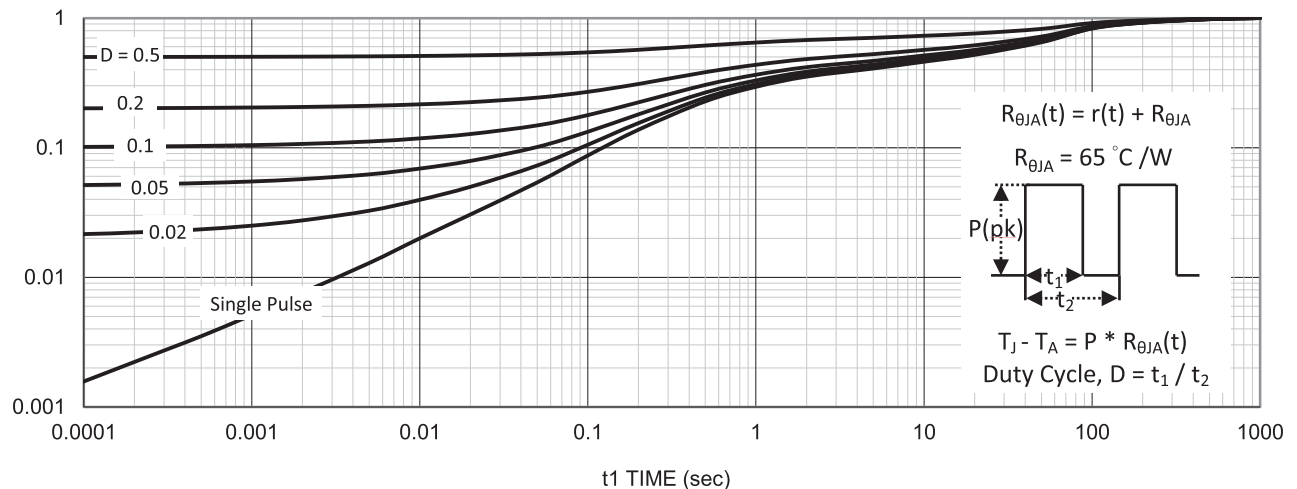
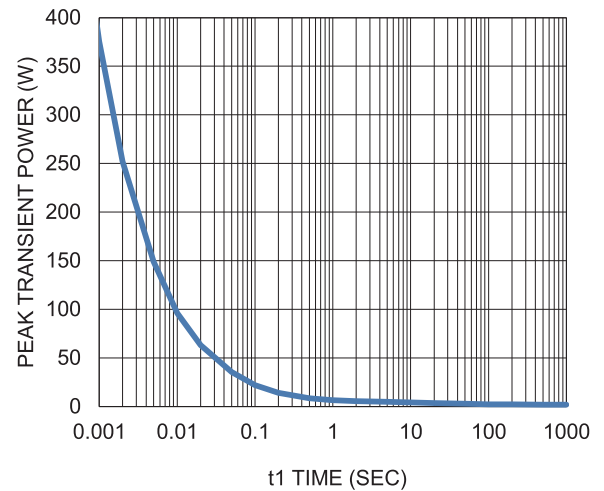
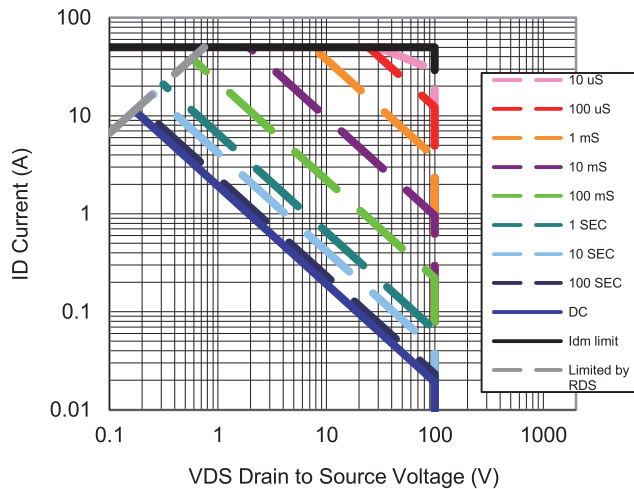
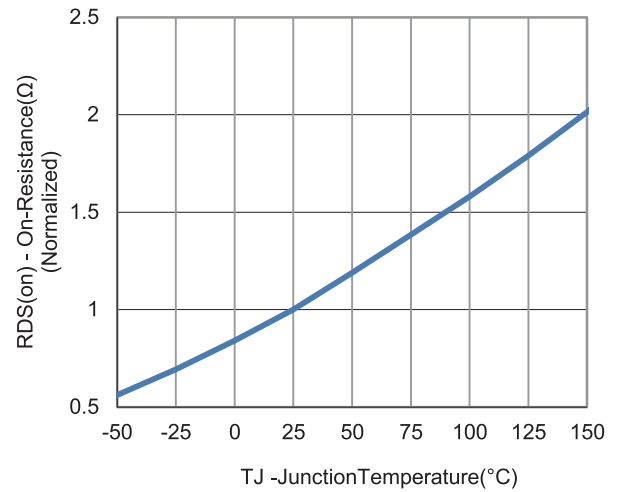
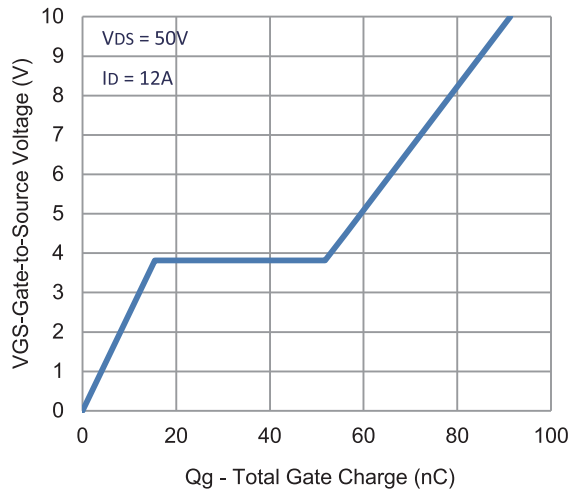
Notes

- Pulse test: PW $\leq 300 \mu s$ duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.

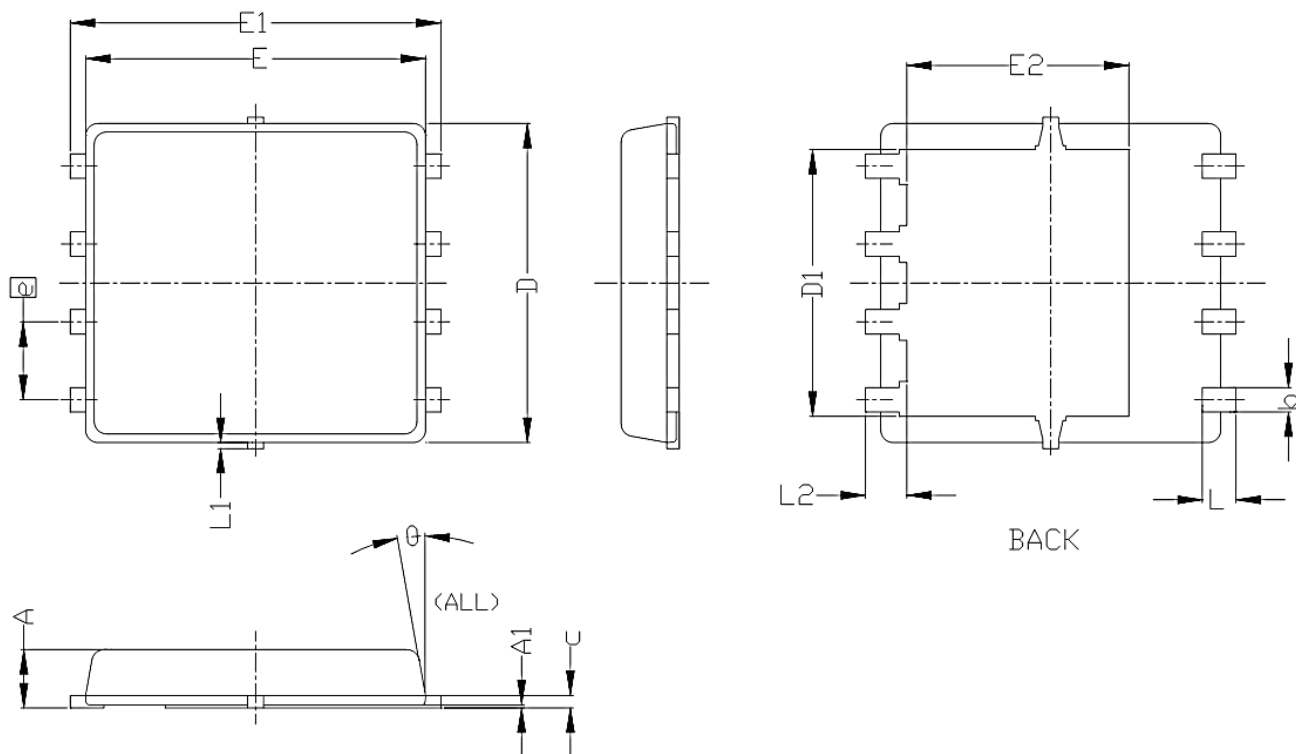
Typical Electrical Characteristics



Typical Electrical Characteristics



Package Information



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.85	0.95	1.00	0.033	0.037	0.039
A1	0.00	---	0.05	0.000	---	0.002
b	0.30	0.40	0.50	0.012	0.016	0.020
c	0.15	0.20	0.25	0.006	0.008	0.010
D	5.20 BSC			0.205 BSC		
D1	4.35 BSC			0.171 BSC		
E	5.55 BSC			0.219 BSC		
E1	6.05 BSC			0.238 BSC		
E2	3.62 BSC			0.143 BSC		
e	1.27 BSC			0.050 BSC		
L	0.45	0.55	0.65	0.018	0.022	0.026
L1	0	---	0.15	0	---	0.006
L2	0.68 REF			0.027 REF		
θ	0°	---	10°	0°	---	10°